

N-Channel Power MOSFET

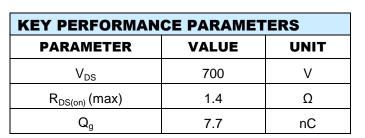
700V, 3.3A, 1.4Ω

FEATURES

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance

APPLICATION

- Power Supply
- Lighting





Sourd Pin 3

TO-251 (IPAK) T



Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _c = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	700	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current (Note 1)	$T_c = 25^{\circ}C$	- I _D	3.3	A
	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 100^{\circ}{\rm C}$		2.0	
Pulsed Drain Current (Note 2)		I _{DM}	9.9	А
Total Power Dissipation @ $T_c = 25^{\circ}C$		P _{DTOT}	38	W
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	64	mJ
Single Pulsed Avalanche Current (Note 3)		I _{AS}	1.6	А
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	R _{eJC}	3.3	°C/W
Junction to Ambient Thermal Resistance	R _{eja}	62	°C/W

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.

TSM70N1R4



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ELECTRICAL SPECIFICA	TIONS (T _c = 25°C unles	ss otherwise no	oted)			
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static (Note 4)						•
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV _{DSS}	700			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V _{GS(TH)}	2	3	4	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 700V, V_{GS} = 0V$	I _{DSS}			1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 1.2A$	R _{DS(ON)}		0.9	1.4	Ω
Dynamic ^(Note 5)						•
Total Gate Charge		Qg		7.7		
Gate-Source Charge	$V_{DS} = 380V, I_{D} = 3.3A,$	Q _{gs}		1.9		nC
Gate-Drain Charge	$V_{GS} = 10V$	Q _{gd}		2.8		
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C _{iss}		370		_
Output Capacitance	f = 1.0MHz	C _{oss}		34		pF
Gate Resistance	F = 1MHz, open drain	R _g		3.4		Ω
Switching (Note 6)					•	
Turn-On Delay Time		t _{d(on)}		14		
Turn-On Rise Time	$V_{DD} = 380V,$	t _r		22		
Turn-Off Delay Time	$R_{GEN} = 25\Omega,$ $I_D = 3.3A, V_{GS} = 10V,$	t _{d(off)}		24		ns
Turn-Off Fall Time		t _f		20		
Source-Drain Diode (Note 4)						
Forward On Voltage	$I_{\rm S} = 3.3$ A, $V_{\rm GS} = 0$ V	V _{SD}			1.4	V
Reverse Recovery Time	$V_{R} = 200V, I_{S} = 2A$	t _{rr}		163		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q _{rr}		1		μC

Notes:

1. Current limited by package

2. Pulse width limited by the maximum junction temperature

3. L = 50mH, I_{AS} = 1.6A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25^oC

4. Pulse test: PW \leq 300µs, duty cycle \leq 2%

5. For DESIGN AID ONLY, not subject to production testing.

6. Switching time is essentially independent of operating temperature.



ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM70N1R4CH C5G	TO-251 (IPAK)	75pcs / Tube
TSM70N1R4CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

Note:

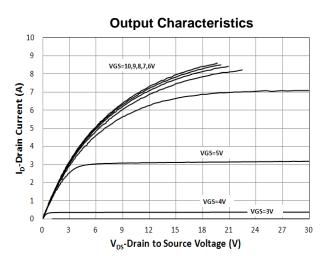
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

2. Halogen-free according to IEC 61249-2-21 definition

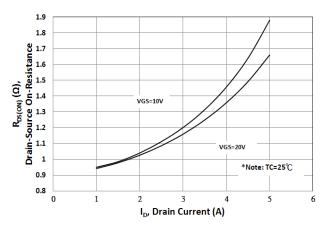


CHARACTERISTICS CURVES

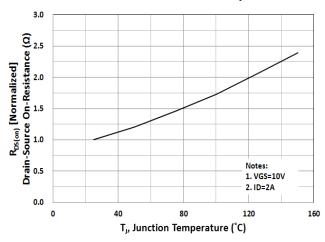
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

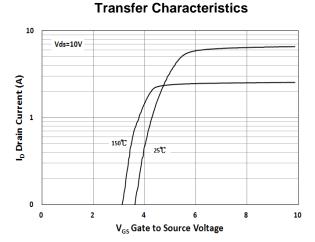


On-Resistance vs. Drain Current

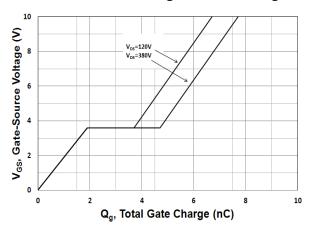


On-Resistance vs. Junction Temperature

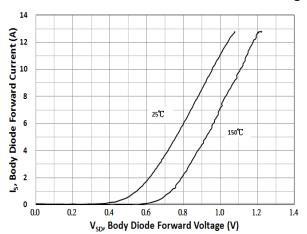




Gate-Source Voltage vs. Gate Charge



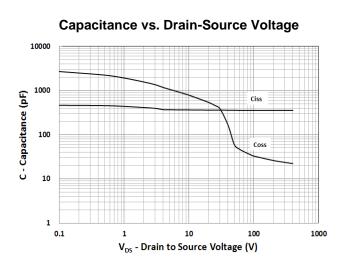
Source-Drain Diode Forward Current vs. Voltage



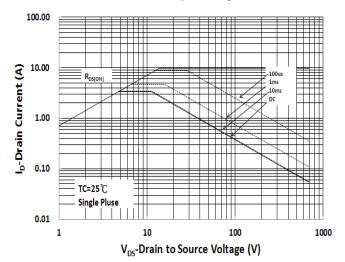


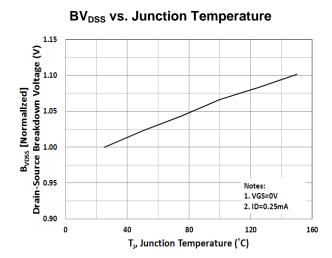
CHARACTERISTICS CURVES

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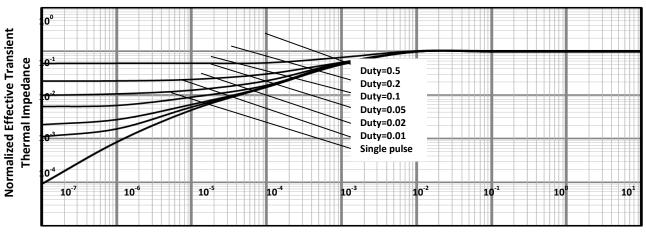


Maximum Safe Operating Area





Normalized Thermal Transient Impedance

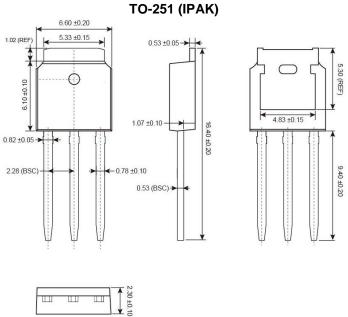




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PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



MARKING DIAGRAM

50	Y = Year CodeM = Month Code for Halogo	en Free Product
70N1R4 YML	O =Jan P =Feb	Q =Mar R =Apr
	S =May T =Jun	U =Jul V =Aug
	W =Sep X =Oct	Y =Nov Z =Dec
#1	L = Lot Code (1~9, A~Z)	

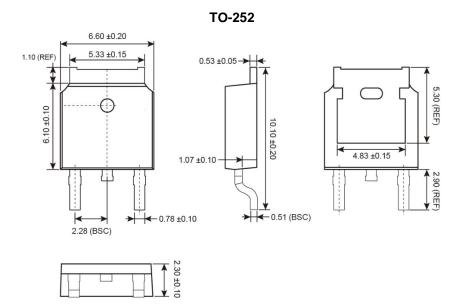




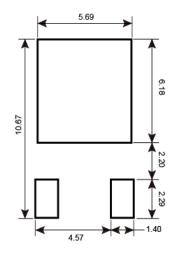
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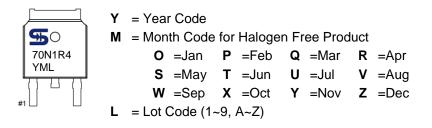
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



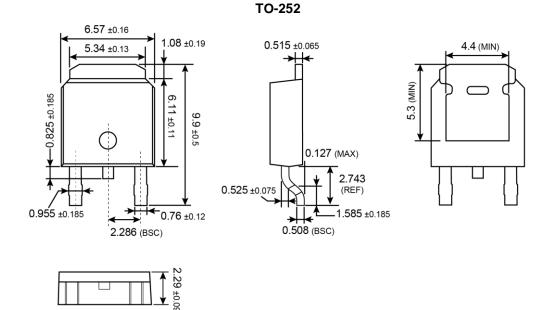
MARKING DIAGRAM



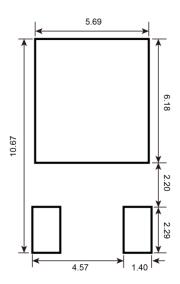




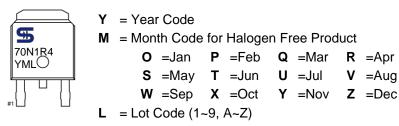
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM





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